SN65C3238, SN75C3238 3-V TO 5.5-V MULTICHANNEL RS-232 COMPATIBLE LINE DRIVER/RECEIVER

SLLS352F - JUNE 1999 - REVISED OCTOBER 2004

 Auto-powerdown Plus Operate With 3-V to 5.5-V V_{CC} Supply 	DB, DW, OR P (TOP \	
 Always-Active Noninverting Receiver Output (ROUT1B) 	C2+ 1 GND 2	28 C1+ 27 V+
 Support Operation From 250 kbit/s to 1 Mbit/s 	C2-[] 3 V-[] 4	26 V _{CC} 25 C1-
Low Standby Current 1 μA Typ	DOUT1 [5	24 DIN1
• External Capacitors 4 × 0.1 μF	DOUT2 6	23 DIN2
Accept 5-V Logic Input With 3.3-V Supply	DOUT3 [] 7 RIN1 [] 8	22 DIN3 21 ROUT1
Inter-Operable With SN65C3243, SN75C3243	RIN2 9 DOUT4 10	20 ROUT2 19 DIN4
RS-232 Bus-Pin ESD Protection Exceeds	RIN3 11	18 ROUT3
±15-kV Using Human-Body Model (HBM)	DOUT5 12	17 DIN5
 Applications 	FORCEON 13	16 ROUT1B
 Battery-Powered Systems, PDAs, Notebooks, Sub-Notebooks, Laptops, 	FORCEOFF [14	15 NVALID

description/ordering information

Modems, and Printers

Palmtop PCs, Hand-Held Equipment,

The 'C3238 devices consist of five line drivers, three line receivers, and a dual charge-pump circuit with ± 15 -kV ESD protection pin to pin (serial-port connection pins, including GND). The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. In addition, these devices include an always-active noninverting output (ROUT1B), which allows applications using the ring indicator to transmit data while the device is powered down. These devices operate at data signaling rates up to 1 Mbit/s and at an increased slew-rate range of 24 V/ μ s to 150 V/ μ s.

ORDERING INFORMATION

TA	PACKAG	PACKAGE†		TOP-SIDE MARKING
	2010 (514)	Tube of 20	SN75C3238DW	750000
	SOIC (DW)	Reel of 1000	SN75C3238DWR	75C3238
−0°C to 70°C	SSOP (DB)	Reel of 2000	SN75C3238DBR	75C3238
	TCCOD (DIAN)	Tube of 50	SN75C3238PW	040000
	TSSOP (PW)	Reel of 2000	SN75C3238PWR	CA3238
	0010 (DIA))	Tube of 20	SN65C3238DW	0500000
	SOIC (DW)	Reel of 1000	SN65C3238DWR	65C3238
-40°C to 85°C	SSOP (DB)	Reel of 2000	SN65C3238DBR	65C3238
	TOOOD (DW)	Tube of 50	SN65C3238PW	ODOGG
	TSSOP (PW)	Reel of 2000	SN65C3238PWR	CB3238

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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SLLS352F - JUNE 1999 - REVISED OCTOBER 2004

description/ordering information (continued)

Flexible control options for power management are featured when the serial-port and driver inputs are inactive. The auto-powerdown plus feature functions when FORCEON is low and $\overline{FORCEOFF}$ is high. During this mode of operation, if the device does not sense valid signal transitions on all receiver and driver inputs for 30 s, the built-in charge-pump and drivers are powered down, reducing the supply current to 1 μ A. By disconnecting the serial port or placing the peripheral drivers off, auto-powerdown plus will occur if there is no activity in the logic levels for the driver inputs. Auto-powerdown plus can be disabled when FORCEON and $\overline{FORCEOFF}$ are high. With auto-powerdown plus enabled, the device automatically activates once a valid signal is applied to any receiver or driver input. $\overline{INVALID}$ is high (valid data) if any receiver input voltage is greater than 2.7 V or less than -2.7 V or has been between -0.3 V and 0.3 V for less than 30 μ s. $\overline{INVALID}$ is low (invalid data) if all receiver input voltages are between -0.3 V and 0.3 V for more than 30 μ s. Refer to Figure 5 for receiver input levels.

Function Tables

EACH DRIVER

		INPU	TS	OUTPUT	
DIN	FORCEON	FORCEOFF	TIME ELAPSED SINCE LAST RIN OR DIN TRANSITION	DOUT	DRIVER STATUS
Х	Х	L	X	Z	Powered off
L	Н	Н	Х	Н	Normal operation with
Н	Н	Н	X	L	auto-powerdown plus disabled
L	L	Н	<30 s	Н	Normal operation with
Н	L	Н	<30 s	L	auto-powerdown plus enabled
L	L	Н	>30 s	Z	Powered off by
Н	L	Н	>30 s	Z	auto-powerdown plus feature

H = high level, L = low level, X = irrelevant, Z = high impedance

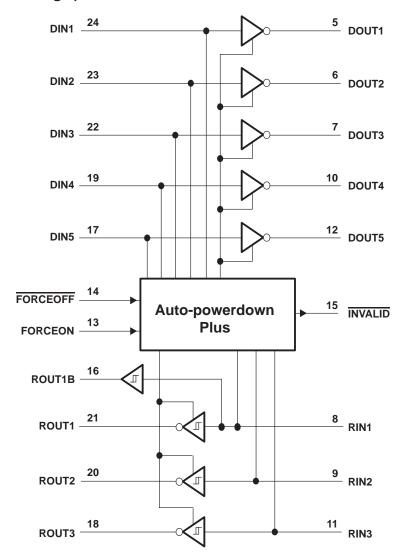
EACH RECEIVER

		INPUT	S	OUTP	UTS	
RIN2	RIN1, RIN3–RIN5	FORCEOFF	TIME ELAPSED SINCE LAST RIN OR DIN TRANSITION	ROUT1B	ROUT	RECEIVER STATUS
L	Χ	L	Х	L	Z	Powered off while
Н	Χ	L	X	Н	Z	ROUT1B is active
L	L	Н	<30 s	L	Н	
L	Н	Н	<30 s	L	L	Normal operation with
Н	L	Н	<30 s	Н	Н	auto-powerdown plus
Н	Н	Н	<30 s	Н	L	disabled/enabled
Open	Open	Н	>30 s	L	Н	

H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = input disconnected or connected driver off



logic diagram (positive logic)



SLLS352F - JUNE 1999 - REVISED OCTOBER 2004

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC} (see Note 1)	–0.3 V to 6 V
Positive output supply voltage range, V+ (see Note 1)	0.3 V to 7 V
Negative output supply voltage range, V- (see Note 1)	0.3 V to –7 V
Supply voltage difference, V+ – V– (see Note 1)	13 V
Input voltage range, V _I : Driver (FORCEOFF, FORCEON)	0.3 V to 6 V
Receiver	–25 V to 25 V
Output voltage range, V _O : Driver	– 13.2 V to 13.2 V
Receiver (INVALID)	0.3 V to V _{CC} + 0.3 V
Package thermal impedance, θ_{JA} (see Notes 2 and 3): DB package	62°C/W
DW package	46°C/W
PW package	62°C/W
Operating virtual junction temperature, T _J	150°C
Storage temperature range, T _{stq}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltages are with respect to network GND.
 - 2. Maximum power dissipation is a function of T_J(max), θ_{JA} , and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
 - 3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 4 and Figure 6)

				MIN	NOM	MAX	UNIT
	Complexable as		$V_{CC} = 3.3 \text{ V}$	3	3.3	3.6	
	Supply voltage		$V_{CC} = 5 V$	4.5	5	5.5	V
.,	Deliver and control bink level in attack	I DIN FORCEOFF FORCEON H	V _{CC} = 3.3 V	2			.,
V_{IH}	Driver and control high-level input voltage	DIN, FORCEOFF, FORCEON	V _{CC} = 5 V	2.4			V
VIL	Driver and control low-level input voltage	DIN, FORCEOFF, FORCEON				8.0	V
٧ _I	Driver and control input voltage	DIN, FORCEOFF, FORCEON		0		5.5	V
٧ _I	Receiver input voltage			-25		25	V
_	T		SN75C3238	0		70	00
TA	Operating free-air temperature	:	SN65C3238	-40		85	°C

NOTE 4: Testing supply conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.15 V; C1–C4 = 0.22 μ F at V_{CC} = 3.3 V \pm 0.3 V; and C1 = 0.047 μ F and C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

	PARAMETER		TEST CONDITIONS	MIN	TYP‡	MAX	UNIT
lį	Input leakage current	FORCEOFF, FORCEON			±0.01	±1	μΑ
		Auto-powerdown plus disabled	No load, FORCEOFF and FORCEON at V _{CC}		0.5	2	mA
loc	Supply current	Powered off	No load, FORCEOFF at GND		1	10	
ICC	Сарру остол	Auto-powerdown plus enabled	No load, FORCEOFF at V _{CC} , FORCEON at GND, All RIN are open or grounded		1	10	μΑ

[‡] All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

NOTE 4: Testing supply conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.15 V; C1–C4 = 0.22 μ F at V_{CC} = 3.3 V ± 0.3 V; and C1 = 0.047 μ F and C2–C4 = 0.33 μF at V_{CC} = 5 V \pm 0.5 V.



SLLS352F - JUNE 1999 - REVISED OCTOBER 2004

DRIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

	PARAMETER	TES	ST CONDITIONS	6	MIN	TYP†	MAX	UNIT
Vон	High-level output voltage	All DOUT at R _L = $3 \text{ k}\Omega$ to	GND		5	5.4		V
VOL	Low-level output voltage	All DOUT at R _L = $3 \text{ k}\Omega$ to	GND		-5	-5.4		٧
lн	High-level input current	VI = VCC				±0.01	±1	μΑ
IIL	Low-level input current	V _I at GND				±0.01	±1	μΑ
	0	V _{CC} = 3.6 V,	VO = 0 V			±35	±60	4
los	Short-circuit output current‡	V _{CC} = 5.5 V,	VO = 0 V			±40	±90	mA
r _O	Output resistance	V_{CC} , V+, and V- = 0 V,	V _O = ±2 V		300	10M		Ω
1	Outrat la also as assument	FORCEOFF = GND	$V_0 = \pm 12 \text{ V},$	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$			±25	
loff	Output leakage current	FURGEOFF = GND	$V_0 = \pm 10 \text{ V},$	V _{CC} = 4.5 V to 5.5 V			±25	μΑ

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

	PARAMETER TEST CONDITIONS		MIN	TYP [†]	MAX	UNIT		
			C _L = 1000 pF		250			
	Maximum data rate (see Figure 1)	$R_L = 3 k\Omega$, One DOUT switching	$C_L = 250 \text{ pF},$	$V_{CC} = 3 V \text{ to } 4.5 V$	1000			kbit/s
	(See Figure 1)	One Boot switching	$C_L = 1000 pF$,	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	1000			
tsk(p)	Pulse skew§	$C_L = 150 \text{ pF to } 2500 \text{ pF},$	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega, 5$	See Figure 2		25		ns
SR(tr)	Slew rate, transition region (see Figure 1)	C _L = 150 pF to 1000 pF,	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$	V _{CC} = 3.3 V	18		150	V/μs

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.



^{\$} Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.

NOTE 4: Testing supply conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.15 V; C1–C4 = 0.22 μ F at V_{CC} = 3.3 V \pm 0.3 V; and C1 = 0.047 μ F and C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

[§] Pulse skew is defined as |tpLH - tpHL| of each channel of the same device.

NOTE 4: Testing supply conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.15 V; C1–C4 = 0.22 μ F at V_{CC} = 3.3 V \pm 0.3 V; and C1 = 0.047 μ F and C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

RECEIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

	PARAMETER	TEST CONDITIONS	MIN	TYP [†]	MAX	UNIT
Vон	High-level output voltage	I _{OH} = -1 mA	V _{CC} – 0.6 V	V _{CC} – 0.1 V		V
VOL	Low-level output voltage	I _{OL} = 1.6 mA			0.4	V
.,	Design as the format three should reduce to	V _{CC} = 3.3 V		1.5	2.4	
V _{IT+}	Positive-going input threshold voltage	V _{CC} = 5 V		1.8	2.4	٧
.,	No netter material tendent through a laboration	V _{CC} = 3.3 V	0.6	1.2		.,
V _{IT} _	Negative-going input threshold voltage	V _{CC} = 5 V	0.8	1.5		V
V _{hys}	Input hysteresis (V _{IT+} - V _{IT-})			0.3		V
l _{off}	Output leakage current (except ROUT1B)	FORCEOFF = 0 V		±0.05	±10	μΑ
rį	Input resistance	$V_1 = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4)

	PARAMETER	TEST CONDITIONS	MIN T	гүр† МАХ	UNIT
^t PLH	Propagation delay time, low- to high-level output	0 450 5 0 5 5 7 7 9		150	ns
tPHL	Propagation delay time, high- to low-level output	C _L = 150 pF, See Figure 3		150	ns
ten	Output enable time	0 450 5 5 0 0 0 5		200	ns
t _{dis}	Output disable time	$C_L = 150 \text{ pF}, R_L = 3 \text{ k}\Omega, \text{See Figure 4}$		200	ns
tsk(p)	Pulse skew‡	See Figure 3		50	ns

 $[\]overline{\dagger}$ All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.



NOTE 4: Testing supply conditions are C1–C4 = $0.1~\mu\text{F}$ at V_{CC} = $3.3~V \pm 0.15~V$; C1–C4 = $0.22~\mu\text{F}$ at V_{CC} = $3.3~V \pm 0.3~V$; and C1 = $0.047~\mu\text{F}$ and C2–C4 = $0.33~\mu\text{F}$ at V_{CC} = $5~V \pm 0.5~V$.

[‡] Pulse skew is defined as |tpLH - tpHL| of each channel of the same device.

NOTE 4: Testing supply conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.15 V; C1–C4 = 0.22 μ F at V_{CC} = 3.3 V \pm 0.3 V; and C1 = 0.047 μ F and C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

SLLS352F - JUNE 1999 - REVISED OCTOBER 2004

AUTO-POWERDOWN PLUS SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	TEST CONDITIONS	MIN	TYP [†]	MAX	UNIT
V _{T+(valid)}	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND, FORCEOFF = V _{CC}			2.7	V
VT–(valid)	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND, FORCEOFF = V _{CC}	-2.7			V
VT(invalid)	Receiver input threshold for INVALID low-level output voltage	FORCEON = GND, FORCEOFF = V _{CC}	-0.3		0.3	V
VOH	INVALID high-level output voltage	I _{OH} = -1 mA, FORCEON = GND, FORCEOFF = V _{CC}	V _{CC} - 0.6			V
VOL	INVALID low-level output voltage	IOL = 1.6 mA, FORCEON = GND, FORCEOFF = V _{CC}			0.4	V

[†] All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

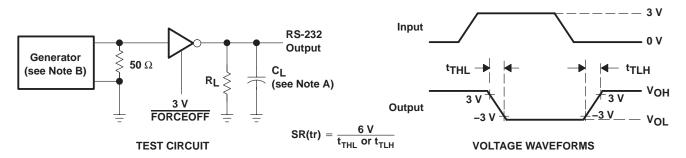
switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	MIN	TYP†	MAX	UNIT
tvalid	Propagation delay time, low- to high-level output		0.1		μs
^t invalid	Propagation delay time, high- to low-level output		50		μs
t _{en}	Supply enable time		25		μs
t _{dis}	Receiver or driver edge to auto-powerdown plus	15	30	60	S

 $[\]dagger$ All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.



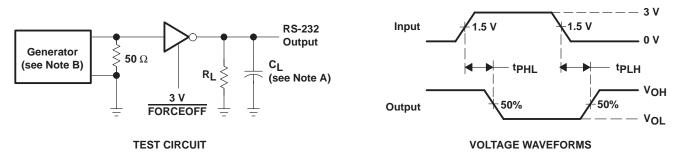
PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_I includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 1 Mbit/s, Z_{Ω} = 50 Ω , 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

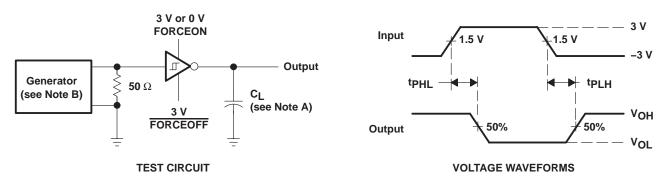
Figure 1. Driver Slew Rate



NOTES: A. C_I includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 1 Mbit/s, $Z_O = 50 \Omega$, 50% duty cycle, $t_T \le 10$ ns, $t_f \le 10$ ns.

Figure 2. Driver Pulse Skew



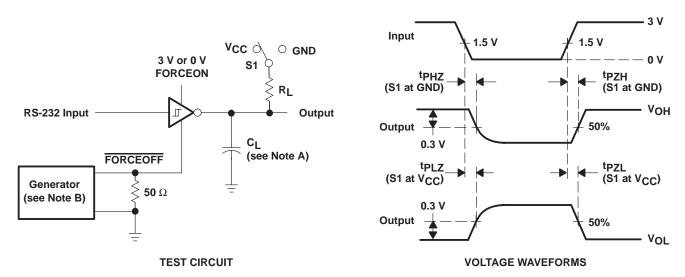
NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: $Z_O = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns. $t_f \le 10$ ns.

Figure 3. Receiver Propagation Delay Times



PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

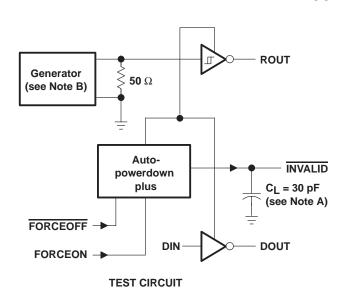
B. The pulse generator has the following characteristics: $Z_0 = 50 \Omega$, 50% duty cycle, $t_f \le 10$ ns. $t_f \le 10$ ns.

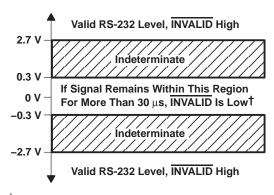
C. tpLz and tpHz are the same as tdis.

D. tpZL and tpZH are the same as ten.

Figure 4. Receiver Enable and Disable Times

PARAMETER MEASUREMENT INFORMATION





 $\mbox{\dagger}$ Auto-powerdown plus disables drivers and reduces supply current to 1 $\mu A.$

- NOTES: A. C_L includes probe and jig capacitance.
 - B. The pulse generator has the following characteristics: PRR = 5 kbit/s, Z_O = 50 Ω , 50% duty cycle, $t_f \le 10$ ns, $t_f \le 10$ ns.

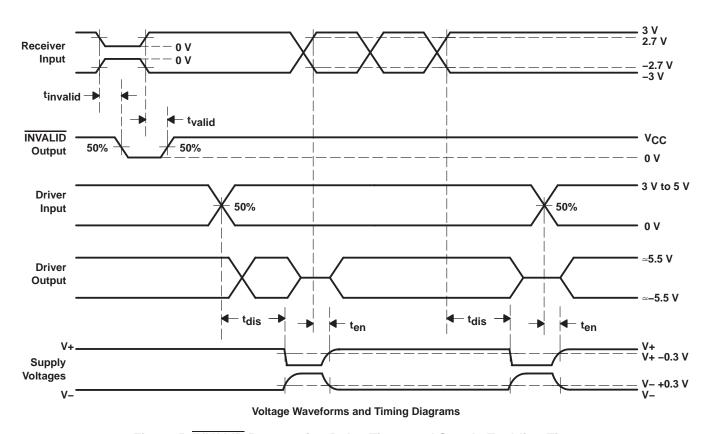
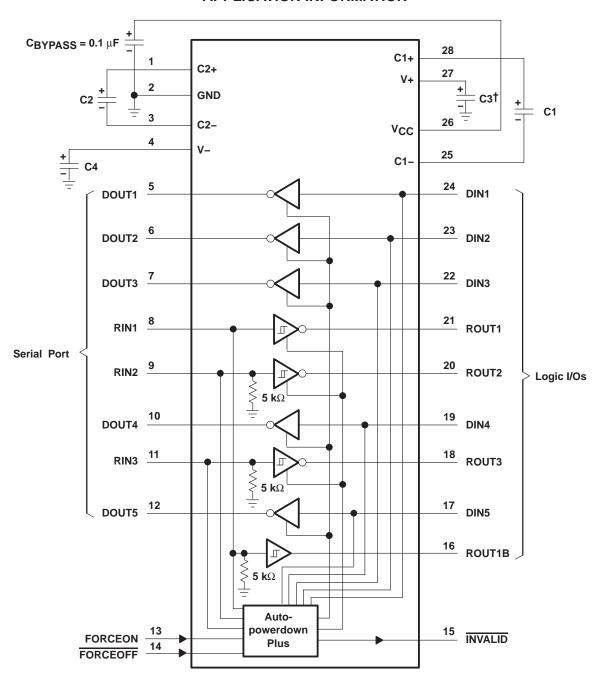


Figure 5. INVALID Propagation Delay Times and Supply Enabling Time



APPLICATION INFORMATION



 $^\dagger\text{C3}$ can be connected to VCC or GND.

NOTE A: Resistor values shown are nominal.

V_{CC} vs CAPACITOR VALUES

VCC	C1	C2, C3, and C4
	0.1 μF 0.22 μF 0.047 μ F 0.22 μF	0.1 μF 0.22 μF 0.33 μF 1 μF

Figure 6. Typical Operating Circuit and Capacitor Values







26-Aug-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65C3238DBR	ACTIVE	SSOP	DB	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3238	Samples
SN65C3238DBRE4	ACTIVE	SSOP	DB	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3238	Samples
SN65C3238DBRG4	ACTIVE	SSOP	DB	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3238	Samples
SN65C3238DWE4	ACTIVE	SOIC	DW	28		TBD	Call TI	Call TI	-40 to 85	65C3238	Samples
SN65C3238DWG4	OBSOLETE	SOIC	DW	28		TBD	Call TI	Call TI	-40 to 85	65C3238	
SN65C3238DWR	ACTIVE	SOIC	DW	28	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3238	Samples
SN65C3238DWRE4	ACTIVE	SOIC	DW	28	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3238	Samples
SN65C3238DWRG4	ACTIVE	SOIC	DW	28	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3238	Samples
SN65C3238PW	ACTIVE	TSSOP	PW	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3238	Samples
SN65C3238PWE4	ACTIVE	TSSOP	PW	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3238	Samples
SN65C3238PWG4	ACTIVE	TSSOP	PW	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3238	Samples
SN65C3238PWR	ACTIVE	TSSOP	PW	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3238	Samples
SN65C3238PWRE4	ACTIVE	TSSOP	PW	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3238	Samples
SN65C3238PWRG4	ACTIVE	TSSOP	PW	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3238	Samples
SN75C3238DBR	ACTIVE	SSOP	DB	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3238	Samples
SN75C3238DBRE4	ACTIVE	SSOP	DB	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3238	Samples
SN75C3238DBRG4	ACTIVE	SSOP	DB	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3238	Samples





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Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN75C3238DW	ACTIVE	SOIC	DW	28	20	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3238	Samples
SN75C3238DWE4	ACTIVE	SOIC	DW	28	20	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3238	Samples
SN75C3238DWG4	ACTIVE	SOIC	DW	28	20	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3238	Samples
SN75C3238DWR	ACTIVE	SOIC	DW	28	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3238	Samples
SN75C3238DWRE4	ACTIVE	SOIC	DW	28	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3238	Samples
SN75C3238DWRG4	ACTIVE	SOIC	DW	28	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3238	Samples
SN75C3238PW	ACTIVE	TSSOP	PW	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3238	Samples
SN75C3238PWE4	ACTIVE	TSSOP	PW	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3238	Samples
SN75C3238PWG4	ACTIVE	TSSOP	PW	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3238	Samples
SN75C3238PWR	ACTIVE	TSSOP	PW	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3238	Samples
SN75C3238PWRE4	ACTIVE	TSSOP	PW	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3238	Samples
SN75C3238PWRG4	ACTIVE	TSSOP	PW	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3238	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.



PACKAGE OPTION ADDENDUM

26-Aug-2013

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above. **Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

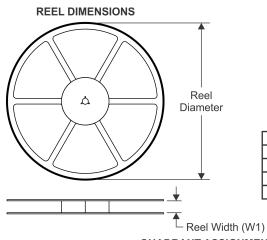
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PACKAGE MATERIALS INFORMATION

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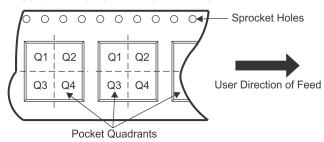
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

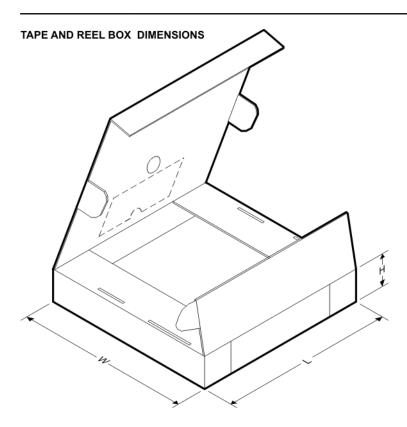
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3238DBR	SSOP	DB	28	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN65C3238DWR	SOIC	DW	28	1000	330.0	32.4	11.35	18.67	3.1	16.0	32.0	Q1
SN65C3238PWR	TSSOP	PW	28	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1
SN75C3238DBR	SSOP	DB	28	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN75C3238DWR	SOIC	DW	28	1000	330.0	32.4	11.35	18.67	3.1	16.0	32.0	Q1
SN75C3238PWR	TSSOP	PW	28	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1

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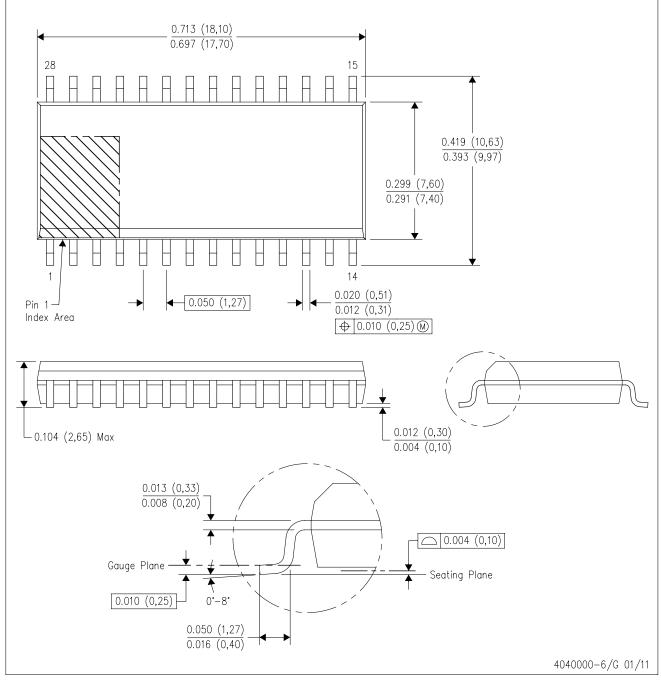


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3238DBR	SSOP	DB	28	2000	367.0	367.0	38.0
SN65C3238DWR	SOIC	DW	28	1000	367.0	367.0	55.0
SN65C3238PWR	TSSOP	PW	28	2000	367.0	367.0	38.0
SN75C3238DBR	SSOP	DB	28	2000	367.0	367.0	38.0
SN75C3238DWR	SOIC	DW	28	1000	367.0	367.0	55.0
SN75C3238PWR	TSSOP	PW	28	2000	367.0	367.0	38.0

DW (R-PDSO-G28)

PLASTIC SMALL OUTLINE



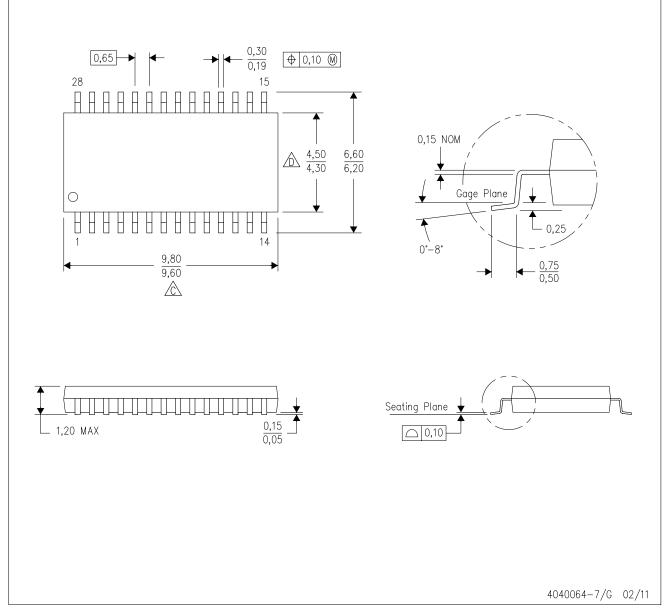
NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AE.



PW (R-PDSO-G28)

PLASTIC SMALL OUTLINE



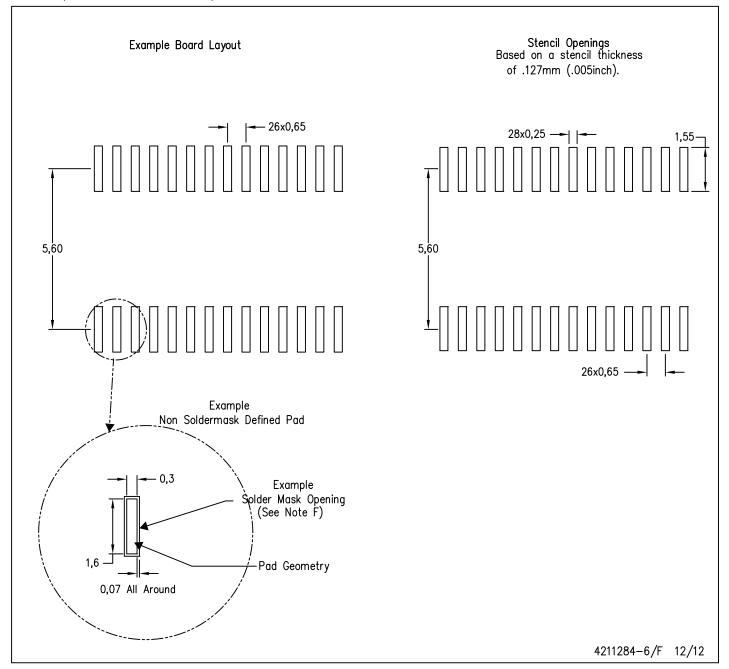
NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G28)

PLASTIC SMALL OUTLINE



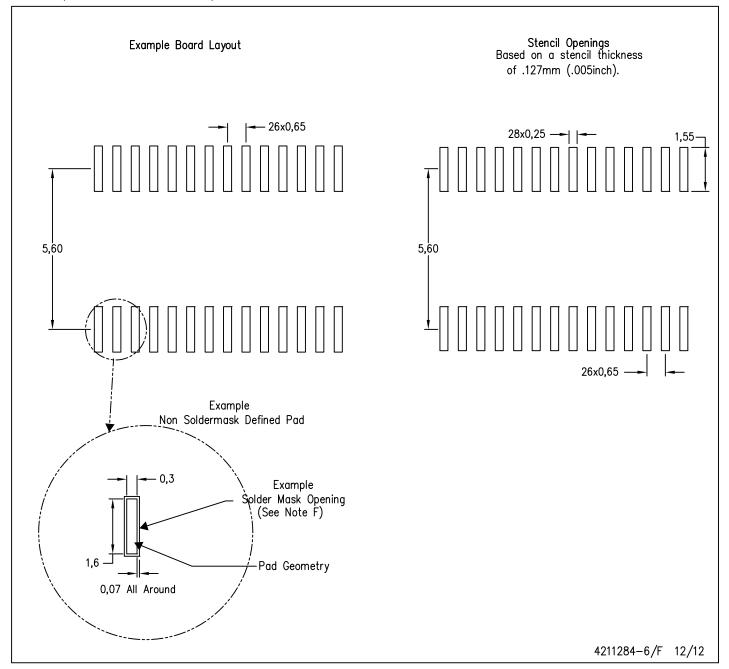
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G28)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-150

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